



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Toshiya UEMURA

Serial No.: 10/694,811

Group Art Unit: 2812

Filed: October 20, 2003

Examiner: Mulpuri, Savitri

For: III GROUP NITRIDE SYSTEM COMPOUND SEMICONDUCTOR LIGHT  
EMITTING ELEMENT AND METHOD OF MAKING SAME

Honorable Commissioner of Patents  
Alexandria, Virginia 22313-1450

**PAPER**

Sir:

Further to an Information Disclosure Statement (IDS) filed January 23, 2004, submitted herewith is an additional form PTO-1449 which includes publication information of the Kazuyuki Tadatomo, et al., reference filed with the above-mentioned IDS. For the Examiner's convenience, a clearer copy of the reference which includes publication information is attached.

Respectfully Submitted,

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(Use several sheets if necessary)

**10/694,811**

**Toshiba UEMURA**

**October 20, 2003**

2812

U.S. PATENT DOCUMENTS

## FOREIGN PATENT DOCUMENTS

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

**Kazuyuki Tadatomo, et al., "High Output Power InGaN Ultraviolet Light-Emitting Diodes Fabricated on Patterned Substrates Using Metalorganic Vapor Phase Epitaxy", Jpn. J. Appl. Phys. Vol. 40 (2001), pp. L583-L585, Part 2, No. 6B, June 15, 2001**

**DATE CONSIDERED**

**EXAMINER:** Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.